#### Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### Listing of Claims:

- 1. (canceled)
- (currently amended) A DRAM cell, according to claim + 10, wherein: the collar is disposed substantially outside of the trench.
- (currently amended) A DRAM cell, according to claim 1 10, wherein:
   the collar is disposed wholly outside of the trench
- (currently amended) A DRAM cell, according to claim ± 10, further comprising:
   a strap the strap being disposed between the node conducting element and the cell transistor.
- (currently amended) A DRAM cell, according to claim 1 10, further comprising:
   a the strap which is being self-aligned with the collar.
- (currently amended) A DRAM cell, according to claim ± 10, further comprising:
   a strap the strap being disposed in the trench at substantially a same depth as the collar.
- (currently amended) A DRAM cell, according to claim ± 10, further comprising:
   a strap the strap being disposed in the trench and laterally surrounded by the collar.
- 8. (canceled)

- 9. (canceled)
- 10. (currently amended) A DRAM cell comprising:

a semiconductor substrate;

a trench extending into the substrate;

a cell capacitor disposed in a bottom portion of the trench;

a cell transistor disposed in a top portion of the trench above the cell capacitor;

a node conducting element connecting the cell capacitor to the cell transistor; and

a collar disposed about the node conducting element between the cell transistor and the

### cell capacitor;

wherein:

the collar is disposed in the substrate, at least partially outside of the trench, between the cell capacitor and the cell transistor;

further comprising:

a strap disposed in the trench and having an outside peripheral surface; and

the collar is laterally adjacent and surrounds the outside peripheral surface of the buried

## strap;

wherein:

the strap is embedded into a top surface of the collar; and

A DRAM cell, according to claim 9, wherein:

the strap extends no higher than the collar.

- 11. (canceled)
- 12. (canceled)
- 13. (canceled)
- 14. (canceled)

- 15. (canceled)
- 16. (canceled)
- 17. (canceled)
- 18. (canceled)
- 19. (canceled)
- 20. (canceled)
- 21. (currently amended) A DRAM cell, according to claim 1 10, further comprising: a recess disposed in a top inside corner of the collar; and the strap extends into the recess in the top inside corner of the collar.
- 22. (currently amended) A DRAM cell comprising:
  - a semiconductor substrate;
  - a trench extending into the substrate;
  - a cell capacitor disposed in a bottom portion of the trench;
  - a cell transistor disposed in a top portion of the trench above the cell capacitor;
  - a node conducting element connecting the cell capacitor to the cell transistor; and
  - a collar disposed about the node conducting element between the cell transistor and the

# cell capacitor;

wherein:

the collar is disposed in the substrate, at least partially outside of the trench, between the cell capacitor and the cell transistor;

further comprising:

a strap disposed in the trench and having an outside peripheral surface; and
the collar is laterally adjacent and surrounds the outside peripheral surface of the buried
strap;

A DRAM cell, according to claim 1, wherein:

the strap is fully vertically embedded in the collar and it is laterally surrounded by the collar.

- 23. (currently amended) A DRAM cell, according to claim 1 22, wherein: the strap is disposed in the trench at substantially a same depth as the collar; and the collar extends deeper into the trench than the strap and and covers a bottom surface of the strap.
- 24. (currently amended) A DRAM cell, according to claim 1 22, wherein: the collar covers a bottom surface of the strap.
- 25. (canceled)
- 26. (canceled)